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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10010484	FILING DATE 11/20/2001	CLASS 257	SUBCLASS 330	GAU 2826	EXAMINER GARDNER, R. J.
APPLICANTS: Hsieh Fwu-luan; So Koon; Amato John; Tsui Yan; TAN TRAN					
**CONTINUING DATA VERIFIED: NO <i>hi</i>					
FOREIGN APPLICATIONS VERIFIED: NO <i>hi</i>					
PG-PUB DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no		USC 119 conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no		ATTORNEY DOCKET NO	
Verified and Acknowledged Examiners's initials <i>TT</i>				GS 150	
TITLE : Trench MOSFET device with polycrystalline silicon source contact structure					
U.S. DEPT. OF COMM. / PAT. & TM. PTO-436L (Rev. 12-94)					

NOTICE OF ALLOWANCE MAILED		TAN TRAN Assistant Examiner <i>07/03</i>		CLAIMS ALLOWED	
				Total Claims 16	Print Claim for O.G. 1
ISSUE FEE		Primary Examiner		DRAWING	
Amount Due	Date Paid			Sheets Drwg. 5	Figs. Drwg. 10
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE		Application Examiner	
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